



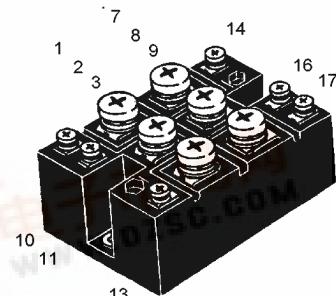
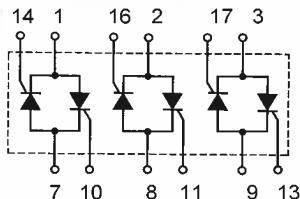
VWO 40

Three Phase AC Controller Modules

$I_{RMS} = 40 \text{ A}$
 $V_{RRM} = 800 - 1600 \text{ V}$

Preliminary data

V_{RSM}	V_{RRM}	Type
V_{DSM}	V_{DRM}	
V	V	
800	800	VWO 40-08io7
1200	1200	VWO 40-12io7
1400	1400	VWO 40-14io7
1600	1600	VWO 40-16io7



Symbol	Test Conditions	Maximum Ratings		
I_{RMS}	$T_c = 85^\circ\text{C}$, 50 - 400 Hz (per phase)	40	A	
I_{TRMS}	$T_{VJ} = T_{VJM}$	29	A	
I_{TAVM}	$T_c = 85^\circ\text{C}$; (180° sine)	18	A	
I_{TSM}	$T_{VJ} = 45^\circ\text{C}$; $V_R = 0$	400 450	A A	
	$T_{VJ} = T_{VJM}$ $V_R = 0$	360 390	A A	
I^2t	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0$	800 850	A^2s A^2s	
	$T_{VJ} = T_{VJM}$ $V_R = 0$	650 640	A^2s A^2s	
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$ $f = 50 \text{ Hz}$, $t_p = 200 \mu\text{s}$ $V_D = 2/3 V_{DRM}$ $I_G = 0.3 \text{ A}$ $di_G/dt = 0.3 \text{ A}/\mu\text{s}$	repetitive, $I_T = 150 \text{ A}$ non repetitive, $I_T = I_{TAVM}$	100	$\text{A}/\mu\text{s}$
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$; $R_{GK} = \infty$; method 1 (linear voltage rise)	$V_{DR} = 2/3 V_{DRM}$	1000	$\text{V}/\mu\text{s}$
P_{GM}	$T_{VJ} = T_{VJM}$ $I_T = I_{TAVM}$	$t_p = 30 \mu\text{s}$ $t_p = 300 \mu\text{s}$	10 5	W
P_{GAVM}			0.5	W
V_{RGM}			10	V
T_{VJ}			-40...+125	$^\circ\text{C}$
T_{VJM}			125	$^\circ\text{C}$
T_{stg}			-40...+125	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS	$t = 1 \text{ min}$	2500	$\text{V}\sim$
	$I_{ISOL} \leq 1 \text{ mA}$	$t = 1 \text{ s}$	3000	$\text{V}\sim$
M_d	Mounting torque (M5) Terminal connection torque (M3; M5)		$5/44 \pm 15 \%$ Nm/lb.in. $1.5/13 \pm 15 \%$ Nm/lb.in.	
Weight	typ.	180	g	

Features

- Thyristor controller for AC (circuit W3C acc. to IEC) for mains frequency
- Package with metal base plate
- Isolation voltage 3000 V~
- Planar passivated chips
- UL applied

Applications

- Switching and control of three phase AC circuits
- Softstart AC motor controller
- Solid state switches
- Light and temperature control

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling
- High power density

Symbol	Test Conditions	Characteristic Values		
I_D, I_R	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	≤	5	mA
V_T	$I_T = 80 \text{ A}; T_{VJ} = 25^\circ\text{C}$	≤	1.65	V
V_{TO}	For power-loss calculations only ($T_{VJ} = 125^\circ\text{C}$)	0.85		V
r_T		15		$\text{m}\Omega$
V_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	≤	1.0	V
I_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	≤	100	mA
V_{GD}	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	≤	0.2	V
I_{GD}		≤	5	mA
I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \mu\text{s}$ $I_G = 0.3 \text{ A}; di_G/dt = 0.3 \text{ A}/\mu\text{s}$	≤	200	mA
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	≤	150	mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 0.3 \text{ A}; di_G/dt = 0.3 \text{ A}/\mu\text{s}$	≤	2	μs
t_q	$T_{VJ} = T_{VJM}; I_T = 20 \text{ A}, t_p = 200 \mu\text{s}; di/dt = -10 \text{ A}/\mu\text{s}$ $V_R = 100 \text{ V}; dv/dt = 15 \text{ V}/\mu\text{s}; V_D = 2/3 V_{DRM}$	typ.	150	μs
R_{thJC}	per thyristor; sine 180°el	1.43		K/W
	per module	0.238		K/W
R_{thJK}	per thyristor; sine 180°el	1.53		K/W
	per module	0.255		K/W
d_s	Creeping distance on surface	8.0		mm
d_A	Creepage distance in air	4.5		mm
a	Max. allowable acceleration	50		m/s^2

Dimensions in mm (1 mm = 0.0394")

